# 3.3 V Quad LVCMOS Differential Line Receiver Translator 

## Description

The NB3N4666C is a quad-channel LVDS line receiver/translator offering data rates up to $400 \mathrm{Mbps}(200 \mathrm{MHz})$ and low power consumption. The NB3N4666C receiver incorporates input fail-safe protection circuit that provides a known output voltage under input open-circuit and terminated ( $100 \Omega$ ) conditions. The four independent inputs accept differential signals such as: M-LVDS, LVDS, LVPECL and HCSL and translates them to a single-ended, 3.3 V LVCMOS.

The NB3N4666C also offers active high and active low enable/disable inputs ( EN and $\overline{\mathrm{EN}}$ ) that allow users to control outputs of all four receivers. These inputs enable or disable the receivers and switch the outputs to an active or high impedance state respectively (see Table 2). The high impedance mode feature helps to reduce the quiescent power consumption to less than 10 mW typical, when the outputs of one or more NB3N4666C devices are multiplexed together.

## Features

- Accepts M-LVDS, LVDS, LVPECL and HCSL Differential Input Signal Levels
- Maximum Data Rate of 400 Mbps
- Maximum Clock Frequency of 200 MHz
- 25 ps Typical Channel-to-Channel Skew
- 3.3 ns Maximum Propagation Delay
- $3.3 \mathrm{~V} \pm 10 \%$ Power Supply
- High Impedance Outputs When Disabled
- Low Quiescent Power < 10 mW Typical
- Supports Open and Terminated Input Fail-safe
- $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ Ambient Operating Temperature
- 16-Pin TSSOP, $5.0 \mathrm{~mm} x 4.4 \mathrm{~mm} \times 1.2 \mathrm{~mm}$
- These are $\mathrm{Pb}-$ Free Devices


## Applications

- Point-to-point Data Transmission
- Backplane Receivers
- Clock Distribution Networks
- Multidrop Buses

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A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week

- = Pb-Free Package
(Note: Microdot may be in either location)


Figure 1. Functional Block Diagram

ORDERING INFORMATION
See detailed ordering and shipping information on page 8 of this data sheet.

Table 1. PIN DESCRIPTION

| Pin TSSOP | Name | I/O | Description |
| :---: | :---: | :---: | :--- |
| 1 | IN1 | Input | Receiver Channel 1 Inverted Input. |
| 2 | IN1 | Input | Receiver Channel 1 Non-inverted Input. |
| 3 | OUT1 | LVCMOS Output | Receiver Channel 1 Output. |
| 4 | EN | Input Enable | Active High Enable. See Table 2 for output enable function. |
| 5 | OUT2 | LVCMOS Output | Receiver Channel 2 Output. |
| 6 | IN2 | Input | Receiver Channel 2 Non-inverted Input. |
| 7 | IN2 | Input | Receiver Channel 2 Inverted Input. |
| 8 | GND | Power | Power Supply Ground (Note 1) |
| 9 | IN3 | Input | Receiver Channel 3 Inverted Input. |
| 10 | IN3 | Input | Receiver Channel 3 Non-inverted Input. |
| 11 | OUT3 | LVCMOS Output | Receiver Channel 3 Output. |
| 12 | EN | Inverted Input <br> Enable | Active Low Enable. Defaults Low when left open; internal pull-down resistor. <br> See Table 2 for output enable function. <br> 13 |
| 14 | OUT4 | LVCMOS Output | Receiver Channel 4 Output. |
| 15 | IN4 | Input | Receiver Channel 4 Non-inverted Input. |
| 16 | VCC | Input | Receiver Channel 4 Inverted Input. |

1. All $\mathrm{V}_{\mathrm{CC}}$ and GND pins must be externally connected to a power supply for proper operation. Bypass each supply pin with $0.01 \mu \mathrm{~F}$ to GND .


Figure 2. TSSOP-16 Pinout (Top View)

## NB3N4666C

Table 2. OUTPUT ENABLE FUNCTION

| ENABLES |  | INPUTS | OUTPUT |
| :---: | :---: | :---: | :---: |
| EN | EN | $\mathbf{I N}, \mathbf{I N}$ | OUT |
| L | H | X | Z |
| All other combinations of ENABLE <br> inputs | $\mathrm{V}_{\mathrm{ID}} \geq 100 \mathrm{mV}$ | H |  |
|  | $\mathrm{V}_{\text {ID }} \leq-100 \mathrm{mV}$ | L |  |
|  | Full Fail-safe OPEN or Terminated | H |  |

## Fail-Safe Feature

The multi-level receiver's internal fail-safe circuitry is designed to provide fail-safe protection for floating/open or terminated receiver inputs, and will output a stable High-level voltage state.

Open Input Pins. The NB3N4666C is a quad receiver device, and if an application requires only 1,2 or 3 receivers, the unused channel(s) inputs should be left OPEN. The internal input circuitry will ensure a HIGH stable output state for open inputs.

Terminated Input. If the driver to the input is disconnected, in a TRI-STATE or power-off condition, the output will again be in a HIGH state, even with a $100-\Omega$ termination resistor across the input pins.
Do not connect unused receiver inputs to ground or any other voltages.


Figure 3. Receiver Differential Input Voltage Showing Transition Region

Table 3. ATTRIBUTES (Note 2)

| Characteristics |  | Value |
| :--- | :--- | :---: |
| ESD Protection | Human Body Model | 6 kV |
|  | Charged Device Model | 500 V |
| $\mathrm{C}_{\text {IN }}$ - Input Capacitance | 4 pF typical |  |
| $\mathrm{R}_{\mathrm{IN}}$ - Input Impedance | $>10 \mathrm{k} \Omega$ |  |
| $\mathrm{R}_{\text {PD }}$ - Inverted Input Enable Pull-down Resistor | $800 \mathrm{k} \Omega$ |  |
| Moisture Sensitivity | Level 1 |  |
| Flammability Rating | UL 94 V-0 @ 0.125 in |  |
| Transistor Count | 621 |  |
| Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test |  |  |

2. For additional information, see Application Note AND8003/D.

Table 4. MAXIMUM RATINGS

| Symbol | Parameter | Condition 1 | Condition 2 | Rating | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{\text {CC }}$ | Supply Voltage Range | GND $=0 \mathrm{~V}$ |  | 4.6 | V |
| $\mathrm{V}_{\text {IN }}$ | Input Voltage Range | GND $=0 \mathrm{~V}$ |  | -0.5 to VCC +0.5 | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range |  |  | -40 to +85 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | Storage Temperature Range |  |  | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\text {JA }}$ | Thermal Resistance (Junction-to-Ambient) | 0 lfpm | TSSOP-16 | 138 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
|  |  | 500 lfpm | TSSOP-16 | 108 |  |
| $\theta_{\text {Jc }}$ | Thermal Resistance (Junction-to-Case) | 2S2P | TSSOP-16 | 33-36 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\mathrm{T}_{\text {sol }}$ | Wave Solder (Pb-Free) |  |  | 265 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 5. DC CHARACTERISTICS $\left(\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} \pm 10 \% ; \mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}\right.$ to $\left.+85^{\circ} \mathrm{C}\right)$

| Symbol | Characteristic | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| POWER SUPPLY |  |  |  |  |  |
| $\mathrm{V}_{\mathrm{CC}}$ | Power Supply Voltage | 2.97 | 3.30 | 3.63 | V |
| ICC | No Load Supply, All Receivers Enabled ( $\mathrm{EN}=\mathrm{V}_{\mathrm{CC}}, \mathrm{EN}=\mathrm{GND}$, inputs open) |  | 10 | 15 | mA |
| $\mathrm{I} C \mathrm{CZ}$ | No Load Supply, All Receivers Disabled ( $\mathrm{EN}=\mathrm{GND}$ and $\mathrm{EN}=\mathrm{V}_{\mathrm{CC}}$, inputs open) |  | 3 | 5.5 | mA |
| $\mathrm{P}_{\mathrm{D}}$ | Power Dissipation (Note 6) |  |  | 300 | mW |

LVCMOS OUTPUTS

| $\mathrm{V}_{\mathrm{OH}}$ | Output High Voltage <br> $\mathrm{I}_{\mathrm{OH}}=-0.4 \mathrm{~mA}$, Input Termin | $\mathrm{I}_{\mathrm{OH}}=-0.4 \mathrm{~mA}, \mathrm{~V}_{\mathrm{ID}}=+200 \mathrm{mV}$ ated ( $100 \Omega$ Across Differential Inputs) $\mathrm{I}_{\mathrm{OH}}=-0.4 \mathrm{~mA}$, Input Shorted | $\begin{aligned} & 2.7 \\ & 2.7 \\ & 2.7 \end{aligned}$ | $\begin{aligned} & 3.0 \\ & 3.0 \\ & 3.0 \end{aligned}$ |  | V |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {OL }}$ | Output Low Voltage | $\mathrm{I}_{\text {OL }}=2 \mathrm{~mA}, \mathrm{~V}_{\text {ID }}=-200 \mathrm{mV}$ | GND | 0.1 | 0.25 | V |
| Ios | Output Short Circuit Current (Note 4) | Outputs enabled, $\mathrm{V}_{\text {OUT }}=0 \mathrm{~V}$ | -15 | -48 | -120 | mA |
| Ioz | Output Off State Current | Outputs disabled, $\mathrm{V}_{\text {OUT }}=0 \mathrm{~V}$ or $\mathrm{V}_{\text {CC }}$ | -10 | $\pm 1$ | +10 | $\mu \mathrm{A}$ |

CONTROL INPUTS (EN, EN)

| $\mathrm{V}_{\mathrm{IH}}$ | Input HIGH Voltage | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$ | 2.0 |  | $\mathrm{~V}_{\mathrm{CC}}$ |
| :---: | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{IL}}$ | Input LOW Voltage | $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$ | GND |  | 0.8 |
| $\mathrm{I}_{\mathrm{I}}$ | Input Current | $\mathrm{V}_{\mathrm{IN}}=0$ V or $\mathrm{V}_{\mathrm{CC}}$, other input $=\mathrm{V}_{\mathrm{CC}}$ or 0 V | -10 | V |  |
| $\mathrm{~V}_{\mathrm{CL}}$ | Input Clamp Voltage | $\mathrm{I}_{\mathrm{CL}}=-18 \mathrm{~mA}$ | -1.5 | -0.9 | +10 |

DIFFERENTIAL INPUTS (IN, IN)

| $\mathrm{V}_{\text {CMR }}$ | Input Common Mode Range $\mathrm{V}_{\text {ID }}=200 \mathrm{mV}$ peak to peak; Differential Input Voltage ( $\mathrm{V}_{\text {ID }}$ ) (Notes 3 and 5) (Figures 6 and 7) | 0.1 |  | 2.3 | V |
| :---: | :---: | :---: | :---: | :---: | :---: |
| 1 N | Input Current $\begin{gathered} \mathrm{V}_{\mathrm{IN}}=+2.8 \mathrm{~V}, \mathrm{~V}_{\mathrm{CC}}=3.6 \mathrm{~V} \text { or } 0 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{IN}}=0 \mathrm{~V}, \mathrm{~V}_{\mathrm{CC}}=3.6 \mathrm{~V} \text { or } 0 \mathrm{~V} \\ \mathrm{~V}_{\mathrm{IN}}=+3.63 \mathrm{~V}, \mathrm{~V}_{\mathrm{CC}}=0 \mathrm{~V} \end{gathered}$ | $\begin{aligned} & -25 \\ & -30 \\ & -30 \end{aligned}$ | $\begin{aligned} & \pm 1 \\ & \pm 1 \end{aligned}$ | $\begin{aligned} & +25 \\ & +30 \\ & +30 \end{aligned}$ | $\mu \mathrm{A}$ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
3. Guaranteed by design and characterization. Not tested in production.
4. Output short-circuit current (los) is specified as magnitude only; a minus sign indicates direction only. Note that only one output should be shorted at a time; do not exceed the maximum junction temperature specification $\left(150^{\circ} \mathrm{C}\right)$.
5. The $\mathrm{V}_{\mathrm{CMR}}$ range is reduced for larger $\mathrm{V}_{I D}$. Example: if $\mathrm{V}_{I D}=400 \mathrm{mV}$, the $\mathrm{V}_{C M R}$ is 0.2 V to 2.2 V . $\mathrm{A} \mathrm{V}_{I D}$ up to $\mathrm{V}_{C C}$ may be applied to the $\mathrm{IN} / \mathrm{IN}$ inputs with the Common-Mode voltage set to $\mathrm{V}_{\mathrm{CC}} / 2$. Propagation delay and Differential Pulse skew decrease when $\mathrm{V}_{\mathrm{ID}}$ is increased from 200 mV to 400 mV . Skew specifications apply for $200 \mathrm{mV} \leq \mathrm{V}_{\text {ID }} \leq 800 \mathrm{mV}$ over the common-mode range.
6. Tested with 100 MHz input frequency on all channels, $\mathrm{EN}=\mathrm{V}_{\mathrm{Cc}}, \mathrm{EN}=\mathrm{GND}$.

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Table 6. AC CHARACTERISTICS $\left(\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} \pm 10 \% ; \mathrm{T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}\right.$ to $\left.+85^{\circ} \mathrm{C}\right)$ (Note 7)

| Symbol | Characteristic | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{f}_{\text {MAX }}$ | Maximum Input Clock Frequency (Note 8) All Channels Switching | 200 | 250 |  | MHz |
| f DATAMAX | Maximum Data Rate | 400 |  |  | Mbps |
| $\mathrm{t}_{\mathrm{plh}} / \mathrm{t}_{\text {phl }}$ | Propagation Delay (Note 9) (Figures 5 and 8) | 1.8 |  | 3.3 | ns |
| tSKEW(0-o) | Channel-to-channel Skew (Note 10) | 0 | 25 | 250 | ps |
| $\mathrm{t}_{\text {SKEW }}(\mathrm{pp})$ | Part-to-part Skew (Note 11) |  | 50 | 500 | ps |
| $t_{\text {SKEW (p) }}$ | Pulse Skew $\left\|t_{\text {PHL }}-\mathrm{t}_{\mathrm{PLH}}\right\|, \mathrm{VCM}=\mathrm{V}_{\mathrm{CC}} / 2$ (Note 12) (Figures 5 and 8) | 0 | 50 | 300 | ps |
| $\mathrm{t}_{\mathrm{r}} / \mathrm{t}_{\mathrm{f}}$ | Output Rise/Fall Time, 20\% - 80\% (Figures 5 and 8) |  | 600 | 1200 | ps |
| $\mathrm{T}_{\mathrm{jit}}(\phi)$ | Additive RMS Phase Jitter <br> Integration Range: $12 \mathrm{kHz}-20 \mathrm{MHz}, \mathrm{f}_{\mathrm{C}}=100 \mathrm{MHz}, 25^{\circ} \mathrm{C}, \mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V}$ |  | 161 |  | fs |
| $\mathrm{t}_{\text {plz }} / \mathrm{t}_{\text {phz }}$ | Output Disable Time (Figures 9 and 10) $\quad \mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega$ |  | 10 | 14 | ns |
| $\mathrm{t}_{\mathrm{pzI}} / \mathrm{t}_{\mathrm{pzh}}$ | Output Enable Time (Figures 9 and 10) $\mathrm{R}_{\mathrm{L}}=2 \mathrm{k} \Omega$ |  | 2 | 5 | ns |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
7. Generator waveform for all tests, unless otherwise specified: $\mathrm{f}=50 \mathrm{MHz}, \mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}$ (includes jig capacitance), tr and tf ( $10 \%$ to $90 \%$ ) $\leq 2$ ns for $\mathrm{INx} / \mathrm{INx}$.
8. $\mathrm{f}_{\text {MAX }}$ generator input conditions: $\mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}<1 \mathrm{~ns}(10 \%$ to $90 \%$ ), $50 \%$ duty cycle, differential ( 1.05 V to 1.35 V peak to peak). Output Criteria: $40 \%-60 \%$ duty cycle, $\mathrm{V}_{\mathrm{OL}}(\max 0.4 \mathrm{~V}), \mathrm{V}_{\mathrm{OH}}(\min 2.7 \mathrm{~V}), \mathrm{C}_{\mathrm{L}}=10 \mathrm{pF}$ (stray plus probes)
9. Measured from the differential crosspoint of the input to $\mathrm{V}_{\mathrm{CC}} / 2$ of the output.
10. t $_{\text {SKEW }}(\mathrm{O}-\mathrm{O})$ is defined as skew between outputs of the same device at the same supply voltage and with equal load conditions.
11. $\mathrm{t}_{\text {SKEW (pp) }}$ is defined as skew between outputs on different devices operating at the same supply voltages and with equal load conditions. Using the same type of inputs on each device, the outputs are measured at the differential cross points.
12. $\mathrm{t}_{\mathrm{SKEW}(\mathrm{p})}$ is the magnitude difference in the differential propagation delay time between the positive-going edge and the negative-going edge of the same channel.

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The above phase noise data was captured using Agilent E5052A/B. The data displays the input phase noise and output phase noise used to calculate the additive phase jitter at a specified integration range. The additive RMS phase jitter contributed by the device (integrated between 12 kHz and 20 MHz ) is 161 fs .

The additive RMS phase jitter performance of the fanout buffer is highly dependent on the phase noise of the input source.
To obtain the most precise additive phase noise measurement, it is vital that the source phase noise be notably lower than that of the DUT. If the phase noise of the source is greater than the noise floor of the device under test, the source noise will dominate the additive phase jitter calculation and lead to an incorrect negative result for the additive phase noise within the integration range. The Figure above is a good example of the NB3N4666C source generator phase noise having a significantly lower floor than the DUT and results in an additive phase jitter of 161 fs .

$$
\begin{aligned}
& \text { NB3N4666C Additive RMS Phase Jitter @ } 100 \mathrm{MHz} \\
& \begin{aligned}
12 \mathrm{kHz} \text { to } 20 \mathrm{MHz}=161 \mathrm{fs} \\
\begin{aligned}
\text { Additive RMS Phase Jitter } & =\sqrt{(\text { Source }+ \text { DUT })^{2}-(\text { Source })^{2}} \\
& =\sqrt{(278.49)^{2}-(227.25)^{2}} \\
& =161 \mathrm{fs}
\end{aligned}
\end{aligned} . \begin{array}{l}
\end{array} \\
& \begin{aligned}
\end{aligned} \\
&
\end{aligned}
$$

Figure 4. Typical Phase Noise Plot at $\mathrm{f}_{\text {carrier }}=100 \mathrm{MHz}$ at an Operating Voltage of 3.3 V , Room Temperature

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Figure 5. AC Reference Measurement


Figure 6. Differential Inputs Driven Differentially


Figure 7. $\mathrm{V}_{\mathrm{CMR}}$ Diagram


Figure 8. Receiver Propagation Delay, Rise and Fall Time

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Figure 9. Test Circuit for Receiver Enable/Disable Delay


Figure 10. Receiver Enable/Disable Delay Waveform

ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :---: | :---: | :---: |
| NB3N4666CDTR2G | TSSOP-16 $5.0 \times 4.4 \mathrm{~mm}$ | (Pb-Free) |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.


TSSOP-16
CASE 948F-01
ISSUE B
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SCALE 2:1


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